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[Vishay Semiconductor/Opto Division](#)
[TSSS2600](#)

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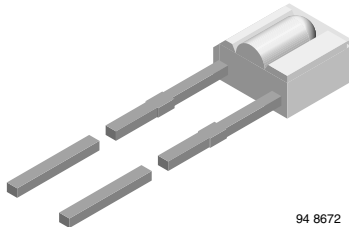


www.vishay.com

TSSS2600

Vishay Semiconductors

Infrared Emitting Diode, 950 nm, GaAs



94 8672

DESCRIPTION

TSSS2600 is an infrared, 950 nm emitting diode in GaAs technology, molded in a miniature, clear plastic package with side view lens.

FEATURES

- Package type: leaded
- Package form: side view
- Dimensions (L x W x H in mm): 3.6 x 2.2 x 5
- Peak wavelength: $\lambda_p = 950$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\phi = \pm 25^\circ$, horizontal
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Package matched with detector TEST2600
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS
COMPLIANT
GREEN
(5-2008)**

Note

** Please see document "Vishay Material Category Policy":
www.vishay.com/doc?99902

APPLICATIONS

- Infrared source in miniature light barriers or reflective sensor systems with short transmission distances and low forward voltage requirements. Matching with silicon PIN photodiodes or phototransistors (e.g. TEST2600)

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	ϕ (deg)	λ_p (nm)	tr (ns)
TSSS2600	2.6	± 25	950	800

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSSS2600	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	Side view

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100 \mu\text{s}$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu\text{s}$	I_{FSM}	2.0	A
Power dissipation		P_V	170	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	Leads not soldered	R_{thJA}	450	K/W



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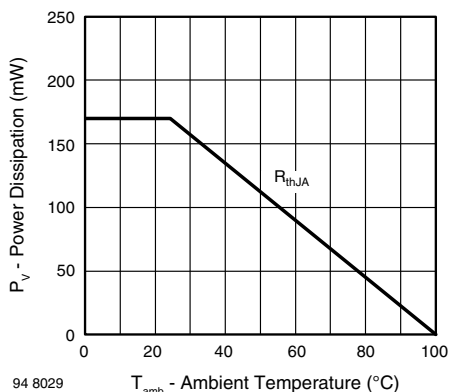


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

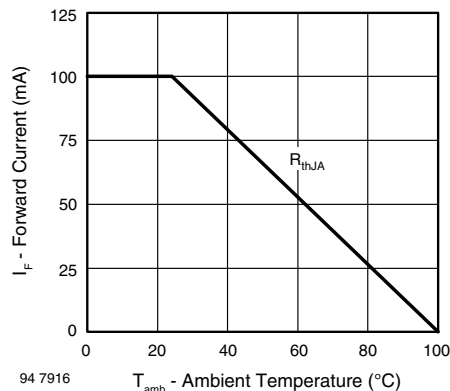


Fig. 1 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F		1.25	1.6	V
	I _F = 1.5 A, t _p = 100 μs	V _F		2.2		V
Temperature coefficient of V _F	I _F = 100 mA	TK _{V_F}		- 1.3		mV/K
Reverse current	V _R = 5 V	I _R			100	μA
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _j		30		pF
Radiant intensity	I _F = 100 mA, t _p = 20 ms	I _e	1	2.6	3	mW/sr
	I _F = 1.5 A, t _p = 100 μs	I _e		25		mW/sr
Radiant power	I _F = 100 mA, t _p = 20 ms	φ _e		20		mW
Temperature coefficient of φ _e	I _F = 100 mA	TKφ _e		- 0.8		%/K
Angle of half intensity	horizontal	φ ₁		± 25		deg
	vertical	φ ₂		± 60		deg
Peak wavelength	I _F = 100 mA	λ _p		950		nm
Spectral bandwidth	I _F = 100 mA	Δλ		50		nm
Temperature coefficient of λ _p	I _F = 100 mA	TKλ _p		0.2		nm/K
Rise time	I _F = 100 mA	t _r		800		ns
	I _F = 1.5 A	t _r		400		ns
Fall time	I _F = 100 mA	t _f		800		ns
	I _F = 1.5 A	t _f		400		ns
Virtual source diameter		d		2		mm



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BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

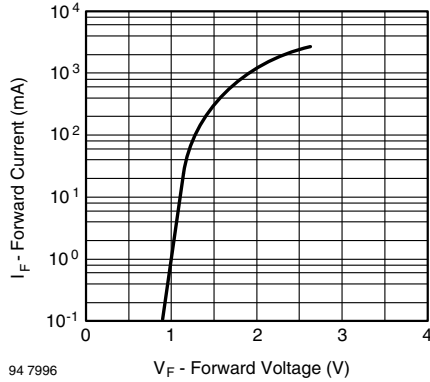


Fig. 2 - Pulse Forward Current vs. Forward Voltage

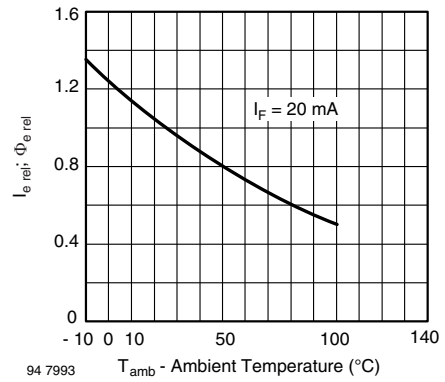


Fig. 5 - Relative Radiant Intensity/Power vs. Ambient Temperature

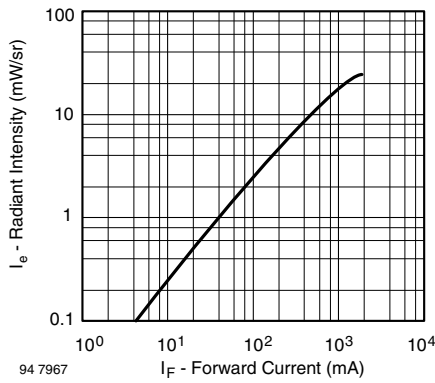


Fig. 3 - Radiant Intensity vs. Forward Current

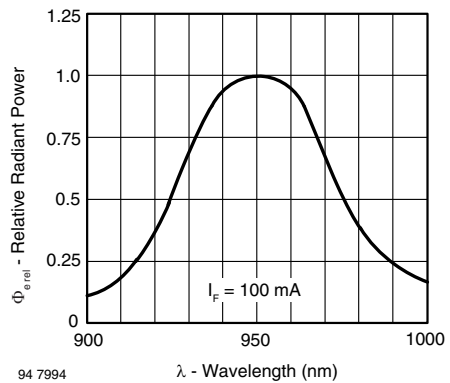


Fig. 6 - Relative Radiant Power vs. Wavelength

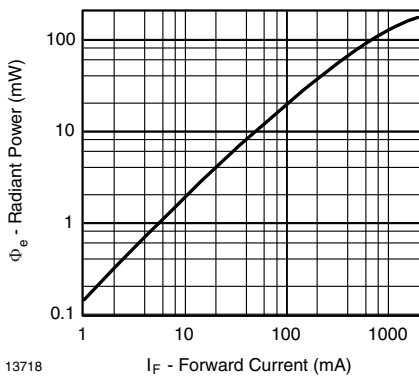


Fig. 4 - Radiant Power vs. Forward Current

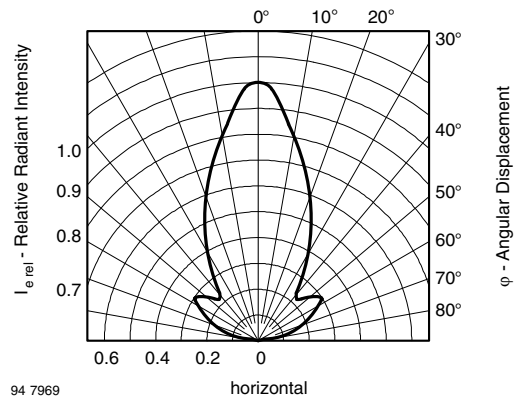


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement



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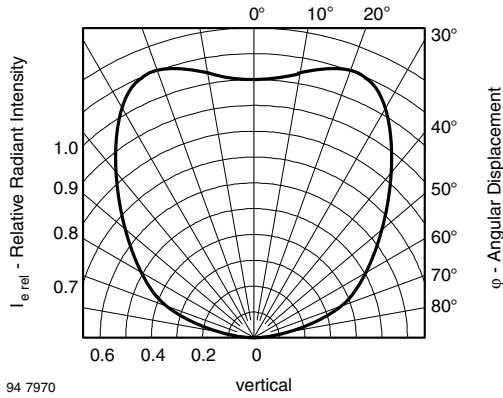
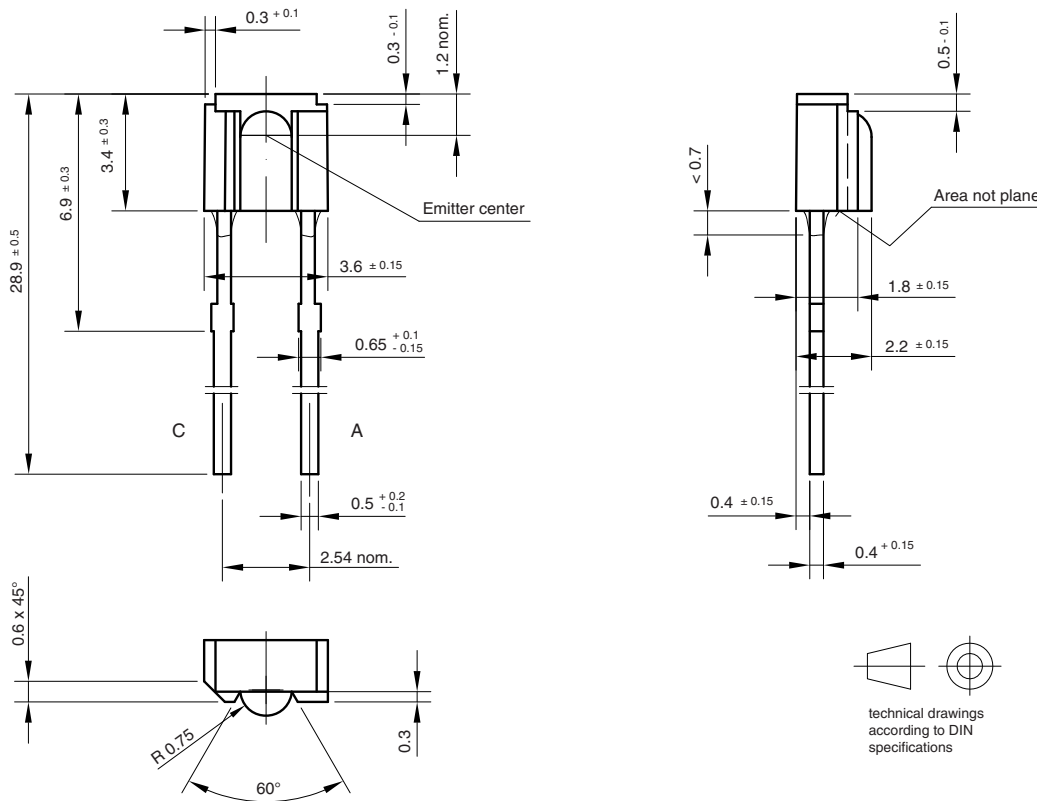


Fig. 2 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5241.01-4
 Issue: 3; 18.04.96
 95 11488



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